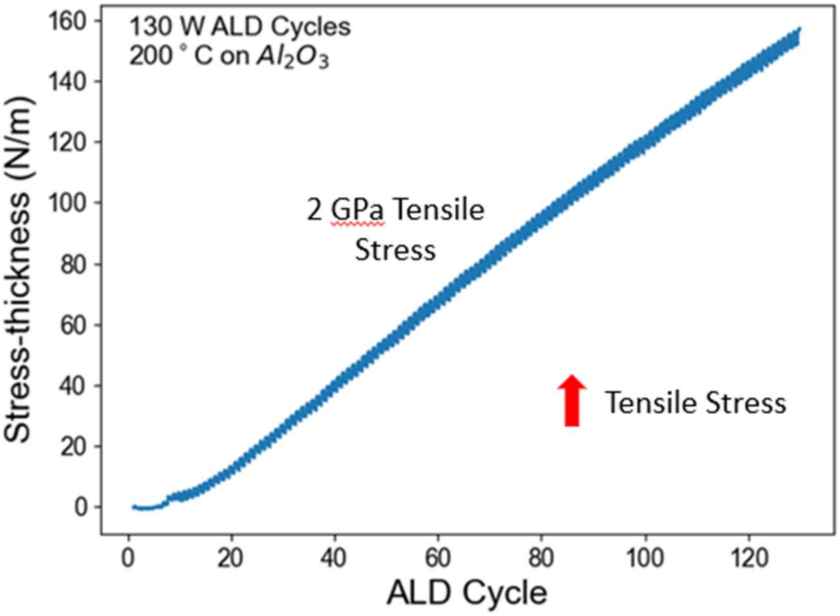

Figure 1: Stress-thickness over 130 W ALD cycles using Si_2H_6 and WF_6 at 200°C. After an initial small compressive stress during nucleation, the film tensile stress is 2 GPa.

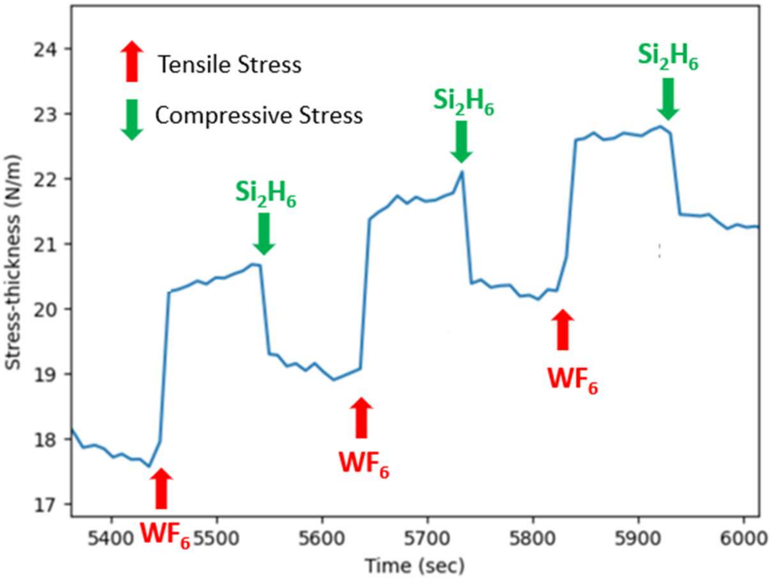

Figure 2: Surface Stresses during W ALD at 200°C. WF_6 exposures result in a large tensile surface stress. The Si_2H_6 exposures then partially release this large tensile surface stress.